



Welcome to <u>E-XFL.COM</u>

Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active	
Number of LABs/CLBs		
Number of Logic Elements/Cells	·	
Total RAM Bits	516096	
Number of I/O	341	
Number of Gates	300000	
Voltage - Supply	1.14V ~ 1.575V	
Mounting Type	Surface Mount	
Operating Temperature	0°C ~ 85°C (TJ)	
Package / Case	484-BGA	
Supplier Device Package	484-FPBGA (23x23)	
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000l-1fg484	

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Microsemi

Global Resources in Low Power Flash Devices

Figure 3-5 shows more detailed global input connections. It shows the global input pins connection to the northwest quadrant global networks. Each global buffer, as well as the PLL reference clock, can be driven from one of the following:

- 3 dedicated single-ended I/Os using a hardwired connection
- 2 dedicated differential I/Os using a hardwired connection (not supported for IGLOO nano or ProASIC3 nano devices)
- The FPGA core



GAA[0:2]: GA represents global in the northwest corner of the device. A[0:2]: designates specific A clock source.



Figure 3-5 • Global I/O Overview



Global Resources in Low Power Flash Devices

External I/O or Local signal as Clock Source

External I/O refers to regular I/O pins are labeled with the I/O convention IOuxwByVz. You can allow the external I/O or internal signal to access the global. To allow the external I/O or internal signal to access the global network, you need to instantiate the CLKINT macro. Refer to Figure 3-4 on page 51 for an example illustration of the connections. Instead of using CLKINT, you can also use PDC to promote signals from external I/O or internal signal to the global network. However, it may cause layout issues because of synthesis logic replication. Refer to the "Global Promotion and Demotion Using PDC" section on page 67 for details.



Figure 3-14 • CLKINT Macro

Using Global Macros in Synplicity

The Synplify[®] synthesis tool automatically inserts global buffers for nets with high fanout during synthesis. By default, Synplicity[®] puts six global macros (CLKBUF or CLKINT) in the netlist, including any global instantiation or PLL macro. Synplify always honors your global macro instantiation. If you have a PLL (only primary output is used) in the design, Synplify adds five more global buffers in the netlist. Synplify uses the following global counting rule to add global macros in the netlist:

- 1. CLKBUF: 1 global buffer
- 2. CLKINT: 1 global buffer
- 3. CLKDLY: 1 global buffer
- 4. PLL: 1 to 3 global buffers
 - GLA, GLB, GLC, YB, and YC are counted as 1 buffer.
 - GLB or YB is used or both are counted as 1 buffer.
 - GLC or YC is used or both are counted as 1 buffer.

Phase Adjustment

The four phases available (0, 90, 180, 270) are phases with respect to VCO (PLL output). The VCO is divided to achieve the user's CCC required output frequency (GLA, YB/GLB, YC/GLC). The division happens after the selection of the VCO phase. The effective phase shift is actually the VCO phase shift divided by the output divider. This is why the visual CCC shows both the actual achievable phase and more importantly the actual delay that is equivalent to the phase shift that can be achieved.

Dynamic PLL Configuration

The CCCs can be configured both statically and dynamically.

In addition to the ports available in the Static CCC, the Dynamic CCC has the dynamic shift register signals that enable dynamic reconfiguration of the CCC. With the Dynamic CCC, the ports CLKB and CLKC are also exposed. All three clocks (CLKA, CLKB, and CLKC) can be configured independently.

The CCC block is fully configurable. The following two sources can act as the CCC configuration bits.

Flash Configuration Bits

The flash configuration bits are the configuration bits associated with programmed flash switches. These bits are used when the CCC is in static configuration mode. Once the device is programmed, these bits cannot be modified. They provide the default operating state of the CCC.

Dynamic Shift Register Outputs

This source does not require core reprogramming and allows core-driven dynamic CCC reconfiguration. When the dynamic register drives the configuration bits, the user-defined core circuit takes full control over SDIN, SDOUT, SCLK, SSHIFT, and SUPDATE. The configuration bits can consequently be dynamically changed through shift and update operations in the serial register interface. Access to the logic core is accomplished via the dynamic bits in the specific tiles assigned to the PLLs.

Figure 4-21 illustrates a simplified block diagram of the MUX architecture in the CCCs.



Note: *For Fusion, bit <88:81> is also needed.

The selection between the flash configuration bits and the bits from the configuration register is made using the MODE signal shown in Figure 4-21. If the MODE signal is logic HIGH, the dynamic shift register configuration bits are selected. There are 81 control bits to configure the different functions of the CCC.

Figure 4-21 • The CCC Configuration MUX Architecture

FlashROM Generation and Instantiation in the Design

The SmartGen core generator, available in Libero SoC and Designer, is the only tool that can be used to generate the FlashROM content. SmartGen has several user-friendly features to help generate the FlashROM contents. Instead of selecting each byte and assigning values, you can create a region within a page, modify the region, and assign properties to that region. The FlashROM user interface, shown in Figure 5-10, includes the configuration grid, existing regions list, and properties field. The properties field specifies the region-specific information and defines the data used for that region. You can assign values to the following properties:

- Static Fixed Data—Enables you to fix the data so it cannot be changed during programming time. This option is useful when you have fixed data stored in this region, which is required for the operation of the design in the FPGA. Key storage is one example.
- Static Modifiable Data—Select this option when the data in a particular region is expected to be static data (such as a version number, which remains the same for a long duration but could conceivably change in the future). This option enables you to avoid changing the value every time you enter new data.
- 3. Read from File—This provides the full flexibility of FlashROM usage to the customer. If you have a customized algorithm for generating the FlashROM data, you can specify this setting. You can then generate a text file with data for as many devices as you wish to program, and load that into the FlashPoint programming file generation software to get programming files that include all the data. SmartGen will optionally pass the location of the file where the data is stored if the file is specified in SmartGen. Each text file has only one type of data format (binary, decimal, hex, or ASCII text). The length of each data file must be shorter than or equal to the selected region length. If the data is shorter than the selected region length, the most significant bits will be padded with 0s. For multiple text files for multiple regions, the first lines are for the first device. In SmartGen, Load Sim. Value From File allows you to load the first device data in the MEM file for simulation.
- 4. Auto Increment/Decrement—This scenario is useful when you specify the contents of FlashROM for a large number of devices in a series. You can specify the step value for the serial number and a maximum value for inventory control. During programming file generation, the actual number of devices to be programmed is specified and a start value is fed to the software.

Figure 5-10 • SmartGen GUI of the FlashROM

Microsemi

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices



Notes:

- Automotive ProASIC3 devices restrict RAM4K9 to a single port or to dual ports with the same clock 180° out of phase (inverted) between clock pins. In single-port mode, inputs to port B should be tied to ground to prevent errors during compile. This warning applies only to automotive ProASIC3 parts of certain revisions and earlier. Contact Technical Support at soc_tech@microsemi.com for information on the revision number for a particular lot and date code.
- 2. For FIFO4K18, the same clock 180° out of phase (inverted) between clock pins should be used.

Figure 6-3 • Supported Basic RAM Macros

SRAM Features

RAM4K9 Macro

RAM4K9 is the dual-port configuration of the RAM block (Figure 6-4). The RAM4K9 nomenclature refers to both the deepest possible configuration and the widest possible configuration the dual-port RAM block can assume, and does not denote a possible memory aspect ratio. The RAM block can be configured to the following aspect ratios: 4,096×1, 2,048×2, 1,024×4, and 512×9. RAM4K9 is fully synchronous and has the following features:

- Two ports that allow fully independent reads and writes at different frequencies
- Selectable pipelined or nonpipelined read
- Active-low block enables for each port
- Toggle control between read and write mode for each port
- · Active-low asynchronous reset
- Pass-through write data or hold existing data on output. In pass-through mode, the data written to the write port will immediately appear on the read port.
- Designer software will automatically facilitate falling-edge clocks by bubble-pushing the inversion to previous stages.



Note: For timing diagrams of the RAM signals, refer to the appropriate family datasheet. *Figure 6-4* • RAM4K9 Simplified Configuration

Signal Descriptions for RAM4K9

Note: Automotive ProASIC3 devices support single-port SRAM capabilities, or dual-port SRAM only under specific conditions. Dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). Since Libero SoC macro libraries support a dual-port macro only, certain modifications must be made. These are detailed below.

The following signals are used to configure the RAM4K9 memory element:

WIDTHA and WIDTHB

These signals enable the RAM to be configured in one of four allowable aspect ratios (Table 6-2 on page 154).

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WIDTHB should be tied to ground.

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Software Support

The SmartGen core generator is the easiest way to select and configure the memory blocks (Figure 6-12). SmartGen automatically selects the proper memory block type and aspect ratio, and cascades the memory blocks based on the user's selection. SmartGen also configures any additional signals that may require tie-off.

SmartGen will attempt to use the minimum number of blocks required to implement the desired memory. When cascading, SmartGen will configure the memory for width before configuring for depth. For example, if the user requests a 256×8 FIFO, SmartGen will use a 512×9 FIFO configuration, not 256×18.

Figure 6-12 • SmartGen Core Generator Interface

Microsemi

I/O Structures in IGLOO and ProASIC3 Devices

Low Power Flash Device I/O Support

The low power flash FPGAs listed in Table 7-1 support I/Os and the functions described in this document.

Table 7-1 • Flash-Based FPGAs

Series	Family [*]	Description	
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology	
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs	
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L	
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L	

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 7-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 7-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

IGLOO and ProASIC3

For boards and cards with three levels of staging, card power supplies must have time to reach their final values before the I/Os are connected. Pay attention to the sizing of power supply decoupling capacitors on the card to ensure that the power supplies are not overloaded with capacitance.

Cards with three levels of staging should have the following sequence:

- Grounds
- Powers
- I/Os and other pins

For Level 3 and Level 4 compliance with the 30K gate device, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 μ s.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 7-12 on page 193). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30K gate devices do not have built-in I/O clamp diodes.

For other IGLOO and ProASIC3 devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 k Ω , and the resulting current is equal to 3.3 V / 45 k Ω = 73 µA for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input LOW when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

Solution 4

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.



Figure 7-12 • Solution 4

I/O Register Combining

Every I/O has several embedded registers in the I/O tile that are close to the I/O pads. Rather than using the internal register from the core, the user has the option of using these registers for faster clock-to-out timing, and external hold and setup. When combining these registers at the I/O buffer, some architectural rules must be met. Provided these rules are met, the user can enable register combining globally during Compile (as shown in the "Compiling the Design" section on page 261).

This feature is supported by all I/O standards.

Rules for Registered I/O Function

- 1. The fanout between an I/O pin (D, Y, or E) and a register must be equal to one for combining to be considered on that pin.
- 2. All registers (Input, Output, and Output Enable) connected to an I/O must share the same clear or preset function:
 - If one of the registers has a CLR pin, all the other registers that are candidates for combining in the I/O must have a CLR pin.
 - If one of the registers has a PRE pin, all the other registers that are candidates for combining in the I/O must have a PRE pin.
 - If one of the registers has neither a CLR nor a PRE pin, all the other registers that are candidates for combining must have neither a CLR nor a PRE pin.
 - If the clear or preset pins are present, they must have the same polarity.
 - If the clear or preset pins are present, they must be driven by the same signal (net).
- 3. Registers connected to an I/O on the Output and Output Enable pins must have the same clock and enable function:
 - Both the Output and Output Enable registers must have an E pin (clock enable), or none at all.
 - If the E pins are present, they must have the same polarity. The CLK pins must also have the same polarity.

In some cases, the user may want registers to be combined with the input of a bibuf while maintaining the output as-is. This can be achieved by using PDC commands as follows:

```
set_io <signal name> -REGISTER yes -----register will combine
set_preserve <signal name> ----register will not combine
```

Weak Pull-Up and Weak Pull-Down Resistors

When the I/O is pulled up, it is connected to the VCCI of its corresponding I/O bank. When it is pulled down, it is connected to GND. Refer to the datasheet for more information.

For low power applications, configuration of the pull-up or pull-down of the I/O can be used to set the I/O to a known state while the device is in Flash*Freeze mode. Refer to the "Flash*Freeze Technology and Low Power Modes in IGLOO and ProASIC3L Devices" chapter in the *IGLOOe FPGA Fabric User's Guide* or *ProASIC3E FPGA Fabric User's Guide* for more information.

The Flash*Freeze (FF) pin cannot be configured with a weak pull-down or pull-up I/O attribute, as the signal needs to be driven at all times.

Output Slew Rate Control

The slew rate is the amount of time an input signal takes to get from logic LOW to logic HIGH or vice versa.

It is commonly defined as the propagation delay between 10% and 90% of the signal's voltage swing. Slew rate control is available for the output buffers of low power flash devices. The output buffer has a programmable slew rate for both HIGH-to-LOW and LOW-to-HIGH transitions. Slew rate control is available for LVTTL, LVCMOS, and PCI-X I/O standards. The other I/O standards have a preset slew value.

The slew rate can be implemented by using a PDC command (Table 8-6 on page 218), setting it "High" or "Low" in the I/O Attribute Editor in Designer, or instantiating a special I/O macro. The default slew rate value is "High."

I/O Cell Architecture

Low power flash devices support DDR in the I/O cells in four different modes: Input, Output, Tristate, and Bidirectional pins. For each mode, different I/O standards are supported, with most I/O standards having special sub-options. For the ProASIC3 nano and IGLOO nano devices, DDR is supported only in the 60 k, 125 k, and 250 k logic densities. Refer to Table 10-2 for a sample of the available I/O options. Additional I/O options can be found in the relevant family datasheet.

DDR Register Type	I/О Туре	I/O Standard	Sub-Options	Comments
Receive Register	Input	Normal	None	3.3 V TTL (default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
			Pull-Up	None (default)
		PCI/PCI-X	None	
		GTL/GTL+	Voltage	2.5 V, 3.3 V (3.3 V default)
		HSTL	Class	I / II (I default)
		SSTL2/SSTL3	Class	I / II (I default)
		LVPECL	None	
		LVDS	None	
Transmit Register	Output	Normal	None	3.3 V TTL (default)
		LVTTL	Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)
			Slew Rate	Low/high (high default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
		PCI/PCI-X	None	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)
		HSTL	Class	I / II (I default)
		SSTL2/SSTL3	Class	I / II (I default)
		LVPECL*	None	
		LVDS*	None	

Table 10-2 • DDR I/O Options

Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.

Microsemi

DDR for Microsemi's Low Power Flash Devices

```
module ddr_test(DIN, CLK, CLR, DOUT);
input DIN, CLK, CLR;
output DOUT;
Inbuf_ddr Inbuf_ddr (.PAD(DIN), .CLR(clr), .CLK(clk), .QR(qr), .QF(qf));
Outbuf_ddr Outbuf_ddr (.DataR(qr),.DataF(qf), .CLR(clr), .CLK(clk),.PAD(DOUT));
INBUF INBUF_CLR (.PAD(CLR), .Y(clr));
INBUF INBUF_CLK (.PAD(CLK), .Y(clk));
```

endmodule

Simulation Consideration

Microsemi DDR simulation models use inertial delay modeling by default (versus transport delay modeling). As such, pulses that are shorter than the actual gate delays should be avoided, as they will not be seen by the simulator and may be an issue in post-routed simulations. The user must be aware of the default delay modeling and must set the correct delay model in the simulator as needed.

Conclusion

Fusion, IGLOO, and ProASIC3 devices support a wide range of DDR applications with different I/O standards and include built-in DDR macros. The powerful capabilities provided by SmartGen and its GUI can simplify the process of including DDR macros in designs and minimize design errors. Additional considerations should be taken into account by the designer in design floorplanning and placement of I/O flip-flops to minimize datapath skew and to help improve system timing margins. Other system-related issues to consider include PLL and clock partitioning.



Programming Flash Devices

List of Changes

Date	Changes	
July 2010	FlashPro4 is a replacement for FlashPro3 and has been added to this chapter. FlashPro is no longer available.	
	The chapter was updated to include SmartFusion devices.	N/A
	The following were deleted:	N/A
	"Live at Power-Up (LAPU) or Boot PROM" section	
	"Design Security" section	
	Table 14-2 • Programming Features for Actel Devices and much of the text in the"Programming Features for Microsemi Devices" section	
	"Programming Flash FPGAs" section	
	"Return Material Authorization (RMA) Policies" section	
	The "Device Programmers" section was revised.	291
	The Independent Programming Centers information was removed from the "Volume Programming Services" section.	292
	Table 11-3 • Programming Solutions was revised to add FlashPro4 and note that FlashPro is discontinued. A note was added for FlashPro Lite regarding power supply requirements.	293
	Most items were removed from Table 11-4 • Programming Ordering Codes, including FlashPro3 and FlashPro.	294
	The "Programmer Device Support" section was deleted and replaced with a reference to the Microsemi SoC Products Group website for the latest information.	294
	The "Certified Programming Solutions" section was revised to add FlashPro4 and remove Silicon Sculptor I and Silicon Sculptor 6X. Reference to <i>Programming and Functional Failure Guidelines</i> was added.	294
	The file type *.pdb was added to the "Use the Latest Version of the Designer Software to Generate Your Programming File (recommended)" section.	295
	Instructions on cleaning and careful insertion were added to the "Perform Routine Hardware Self-Diagnostic Test" section. Information was added regarding testing Silicon Sculptor programmers with an adapter module installed before every programming session verifying their calibration annually.	295
	The "Signal Integrity While Using ISP" section is new.	296
	The "Programming Failure Allowances" section was revised.	296

The following table lists critical changes that were made in each revision of the chapter.

Security Architecture

Fusion, IGLOO, and ProASIC3 devices have been designed with the most comprehensive programming logic design security in the industry. In the architecture of these devices, security has been designed into the very fabric. The flash cells are located beneath seven metal layers, and the use of many device design and layout techniques makes invasive attacks difficult. Since device layers cannot be removed without disturbing the charge on the programmed (or erased) flash gates, devices cannot be easily deconstructed to decode the design. Low power flash devices are unique in being reprogrammable and having inherent resistance to both invasive and noninvasive attacks on valuable IP. Secure, remote ISP is now possible with AES encryption capability for the programming file during electronic transfer. Figure 12-2 shows a view of the AES decryption core inside an IGLOO device; Figure 12-3 on page 304 shows the AES decryption core inside a Fusion device. The AES core is used to decrypt the encrypted programming file when programming.





Figure 12-2 • Block Representation of the AES Decryption Core in IGLOO and ProASIC3 Devices



Security in Low Power Flash Devices

STAPL File with AES Encryption

- Does not contain AES key / FlashLock Key information
- · Intended for transmission through web or service to unsecured locations for programming

```
NOTE "CREATOR" "Designer Version: 6.1.1.108";
NOTE "DEVICE" "A3PE600";
NOTE "DACKAGE" "208 PQFP";
NOTE "DATE" "2005/04/08";
NOTE "DATE" "2005/04/08";
NOTE "STAPL_VERSION" "JESD71";
NOTE "IDCODE" "$123261CF";
NOTE "DESIGN" "counter32";
NOTE "DESIGN" "counter32";
NOTE "CHECKSUM" "$EF57";
NOTE "SAVE_DATA" "FROMStream";
NOTE "SAVE_DATA" "FROMStream";
NOTE "SECURITY" "ENCRYPT FROM CORE ";
NOTE "ALG_VERSION" "1";
NOTE "MAX_FREQ" "20000000";
NOTE "SILSIG" "$00000000";
```

Conclusion

The new and enhanced security features offered in Fusion, IGLOO, and ProASIC3 devices provide stateof-the-art security to designs programmed into these flash-based devices. Microsemi low power flash devices employ the encryption standard used by NIST and the U.S. government—AES using the 128-bit Rijndael algorithm.

The combination of an on-chip AES decryption engine and FlashLock technology provides the highest level of security against invasive attacks and design theft, implementing the most robust and secure ISP solution. These security features protect IP within the FPGA and protect the system from cloning, wholesale "black box" copying of a design, invasive attacks, and explicit IP or data theft.

Term	Explanation	
Security Header programming file	Programming file used to program the FlashLock Pass Key and/or AES key into the device to secure the FPGA, FlashROM, and/or FBs.	
AES (encryption) key	128-bit key defined by the user when the AES encryption option is set in the Microsemi Designer software when generating the programming file.	
FlashLock Pass Key	128-bit key defined by the user when the FlashLock option is set in the Microsemi Designer software when generating the programming file.	
	The FlashLock Key protects the security settings programmed to the device. Once a device is programmed with FlashLock, whatever settings were chosen at that time are secure.	
FlashLock	The combined security features that protect the device content from attacks. These features are the following:	
	Flash technology that does not require an external bitstream to program the device	
	 FlashLock Pass Key that secures device content by locking the security settings and preventing access to the device as defined by the user 	
	 AES key that allows secure, encrypted device reprogrammability 	

Glossary

References

National Institute of Standards and Technology. "ADVANCED ENCRYPTION STANDARD (AES) Questions and Answers." 28 January 2002 (10 January 2005).

See http://csrc.nist.gov/archive/aes/index1.html for more information.



In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X

signal deactivated, which also has the effect of disabling the input buffers. The SAMPLE/PRELOAD instruction captures the status of pads in parallel and shifts them out as new data is shifted in for loading into the Boundary Scan Register (BSR). When the device is in an unprogrammed state, the OE and output BSR will be undefined; however, the input BSR will be defined as long as it is connected and being used. For JTAG timing information on setup, hold, and fall times, refer to the *FlashPro User's Guide*.

ISP Support in Flash-Based Devices

The flash FPGAs listed in Table 13-1 support the ISP feature and the functions described in this document.

Series	Family [*]	Description	
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology	
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards	
	IGLOO nano	The industry's lowest-power, smallest-size solution	
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities	
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs	
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards	
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities	
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology	
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L	
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L	
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications	
SmartFusion	SmartFusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable microcontroller subsystem (MSS) which includes programmable analog and an ARM® Cortex [™] -M3 hard processor and flash memory in a monolithic device	
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device	
ProASIC	ProASIC	First generation ProASIC devices	
	ProASIC ^{PLUS}	Second generation ProASIC devices	

Table 13-1 • Flash-Based FPGAs Supporting ISP

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 13-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 13-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

ISP Programming Header Information

The FlashPro4/3/3X programming cable connector can be connected with a 10-pin, 0.1"-pitch programming header. The recommended programming headers are manufactured by AMP (103310-1) and 3M (2510-6002UB). If you have limited board space, you can use a compact programming header manufactured by Samtec (FTSH-105-01-L-D-K). Using this compact programming header, you are required to order an additional header adapter manufactured by Microsemi SoC Products Group (FP3-10PIN-ADAPTER-KIT).

Existing ProASIC^{PLUS} family customers who are using the Samtec Small Programming Header (FTSH-113-01-L-D-K) and are planning to migrate to IGLOO or ProASIC3 devices can also use FP3-10PIN-ADAPTER-KIT.

Manufacturer	Part Number	Description
AMP	103310-1	10-pin, 0.1"-pitch cable header (right-angle PCB mount angle)
3M	2510-6002UB	10-pin, 0.1"-pitch cable header (straight PCB mount angle)
Samtec	FTSH-113-01-L-D-K	Small programming header supported by FlashPro and Silicon Sculptor
Samtec	FTSH-105-01-L-D-K	Compact programming header
Samtec	FFSD-05-D-06.00-01-N	10-pin cable with 50 mil pitch sockets; included in FP3- 10PIN-ADAPTER-KIT.
Microsemi	FP3-10PIN-ADAPTER-KIT	Transition adapter kit to allow FP3 to be connected to a micro 10-pin header (50 mil pitch). Includes a 6 inch Samtec FFSD-05-D-06.00-01-N cable in the kit. The transition adapter board was previously offered as FP3-26PIN-ADAPTER and includes a 26-pin adapter for design transitions from ProASIC ^{PLUS} based boards to ProASIC3 based boards.

Table 13-3 • Programming Header Ordering Codes



Note: *Prog_Mode on FlashPro4 is an output signal that goes High during device programming and returns to Low when programming is complete. This signal can be used to drive a system to provide a 1.5 V programming signal to IGLOO nano, ProASIC3L, and RT ProASIC3 devices that can run with 1.2 V core voltage but require 1.5 V for programming. IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only), but IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.

Figure 13-5 • Programming Header (top view)

2. VCC rises to 1.5 V before programming begins.

Figure 14-3 • Programming Algorithm

The oscilloscope plot in Figure 14-3 shows a wider time interval for the programming algorithm and includes the TDI and TMS signals from the FlashPro3. These signals carry the programming information that is programmed into the device and should only start toggling after the V_{CC} core voltage reaches 1.5 V. Again, TRST from FlashPro3 and the V_{CC} core voltage of the IGLOO device are labeled. As shown in Figure 14-3, TDI and TMS are floating initially, and the core voltage is 1.2 V. When a programming command on the FlashPro3 is executed, TRST is driven HIGH and TDI is momentarily driven to ground. In response to the HIGH TRST signal, the circuit responds and pulls the core voltage to 1.5 V. After 100 ms, TRST is briefly driven LOW by the FlashPro software. This is expected behavior that ensures the device JTAG state machine is in Reset prior to programming. TRST remains HIGH for the duration of the programming. It can be seen in Figure 14-3 that the VCC core voltage signal remains at 1.5 V for approximately 50 ms before information starts passing through on TDI and TMS. This confirms that the voltage switching circuit drives the VCC core supply voltage to 1.5 V prior to programming.

sleep 32 static 23 summary 23 product support customer service 387 email 387 My Cases 388 outside the U.S. 388 technical support 387 website 387 programmers 291 device support 294 programming AES encryption 319 basics 289 features 289 file header definition 323 flash and antifuse 291 flash devices 289 glossary 324 guidelines for flash programming 295 header pin numbers 336 microprocessor 349 power supplies 329 security 313 solution 334 solutions 293 voltage 329 volume services 292 programming support 287

R

RAM memory block consumption 163 remote upgrade via TCP/IP 354 routing structure 18

S

security 330 architecture 303 encrypted programming 354 examples 308 features 304 FlashLock 307 FlashROM 137 FlashROM use models 311 in programmable logic 301 overview 301 shutdown mode 32 context save and restore 34 signal integrity problem 337 silicon testing 370 sleep mode 32 context save and restore 34 SmartGen 170 spine architecture 57 spine assignment 68 SRAM features 153 initializing 164 software support 170 usage 157 STAPL player 351 STAPL vs. DirectC 353 static mode 23 switching circuit 344 verification 344 synthesizing 258

Τ

TAP controller state machine 357, 366 tech support ITAR 388 My Cases 388 outside the U.S. 388 technical support 387 transient current VCC 376 VCCI 376 transient current, power-up/-down 375

U

UJTAG CCC dynamic reconfiguration 368 fine tuning 369 macro 365 operation 366 port usage 367 use to read FlashROM contents 363 ULSICC 40 ultra-fast local lines 18

V

variable aspect ratio and cascading 161 VersaNet global networks 49 VersaTile 15 very-long-line resources 19 ViewDraw 257 VREF pins manually assigning 265

W

web-based technical support 387